

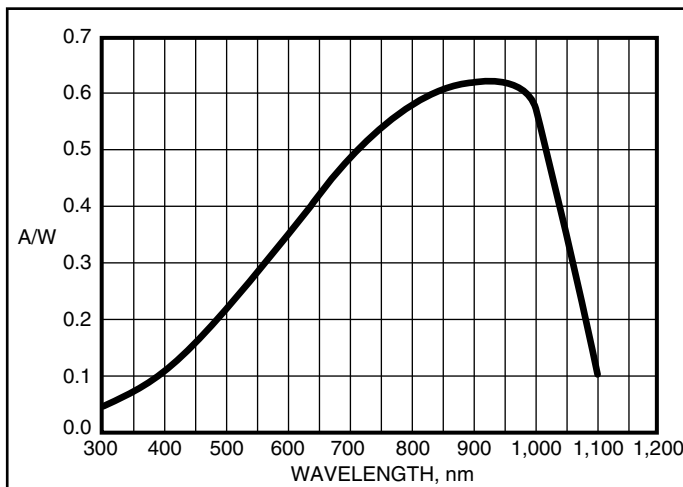
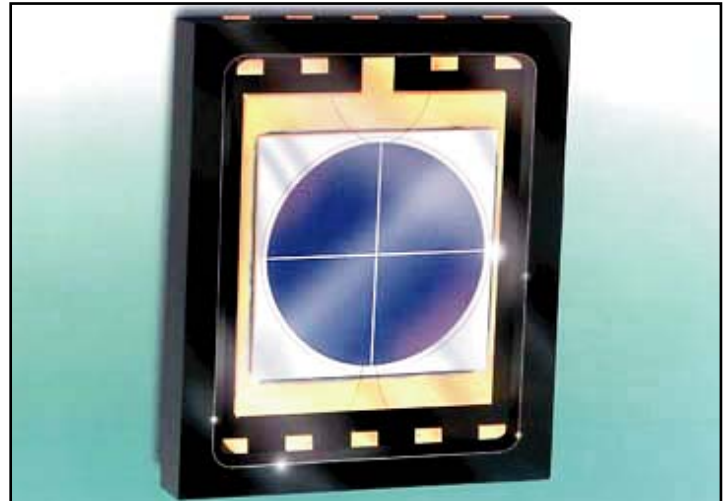


# QP50-6-SM

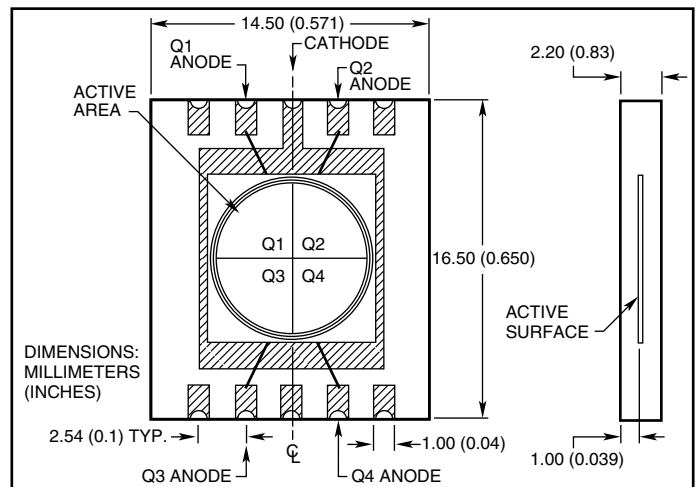
## LARGE AREA QUADRANT SILICON PHOTODIODE QP50-6-SM

QP50-6-SM is a large area quadrant silicon photodiode with a total active area of 50 mm<sup>2</sup>, in a surface mounting package. The part features very small separation between segments of 42 μm. The photodiode may be biased with a maximum of 15 volts. Capacitance per segment is typically 17 pF at 10 volts and the rise time is 45 ns. Applications include laser centering and general automatic light beam aiming devices. The part can be applied to circuit boards using re-flow soldering or conductive epoxy.

This part is also available in a hermetically sealed TO-8 package: P/N QP50-6-TO8.



SPECTRAL RESPONSE



OUTLINE DIMENSIONS

### PHOTODIODE CHARACTERISTICS PER SEGMENT

PART NO.	ACTIVE AREA TOTAL			DARK CURRENT nA @ 10 V		SPECTRAL RESPONSIVITY @ 633 nm A/W	CAPACITANCE PF @		RISE TIME ns @ 10 V AT 865 nm 50 Ω
	mm <sup>2</sup>	DIA mm	SEP μm	TYP	MAX		0V	10V	
QP50-6-SM	50	7.8	42	5.0	10.0	0.45	120	17	45

### ABSOLUTE MAXIMUM RATINGS

DC REVERSE VOLTAGE	PEAK DC CURRENT	STORAGE TEMPERATURE	OPERATING TEMPERATURE	SOLDERING TEMPERATURE
30	10 mA	-40°C to +120°C	-40°C to 105°C	240° for 10 sec.